Photo Couplers Panasonic

### **CND0216A**

### Infrared Optocal Module (IrDA)

Infrared data link for cellular phones, peripheral devices

#### ■ Features

- Compliant with IrDA Ver.1.2
- Light emitting function for remote controller
- Corresponding reflow solder (260°C)
- Ultra-small top view package (1.6 mm × 7.2 mm × 2.6 mm)

#### ■ Type

• GaAlAs LED + IC + PIN Photodiode

#### ■ Absolute Maximum Ratings $T_a = 25$ °C±3°C

Parameter	Symbol	Rating	Unit
Output voltage	Vo	-0.5 to +3.8	V
Input voltage	$V_{\rm I}$	-0.5 to $+3.8$	V
Shutdown input voltage	$V_{\mathrm{SD}}$	-0.5 to +3.8	V
LED operating supply voltage	V <sub>LEDA</sub>	-0.5 to +7.0	V
Pulse forward current *	$I_{FP}$	300	mA
Low level output current	$I_{OL}$	10	mA
Operating ambient temperature	T <sub>opr</sub>	-20 to +70	°C
Storage temperature	T <sub>stg</sub>	-30 to +85	°C

Note) \*: tw  $\leq$  90  $\mu$ s, Duty  $\leq$  25 %

### ■ Operation Condition

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Operating supply voltage	V <sub>CC</sub>		2.8		4.5	V
Input/output supply voltage	V <sub>IO</sub>		1.5	1.8	3.0	V

### ■ Electrical-Optical Characteristics $V_{CC} = 3.2 \text{ V}, V_{IO} = 1.8 \text{ V}, T_a = 25^{\circ}\text{C} \pm 3^{\circ}\text{C}$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
High level supply current *1	$I_{CCH}$	$E_I = 0, V_I = 0.5 \text{ V}, V_{SD} \le 0.5 \text{ V}$		110	150	μΑ
Low level supply current *1	I <sub>CCL</sub>	$E_I = 3 \text{ mW/cm}^2$ , $V_I = 0.5 \text{ V}$ , $V_{SD} \le 0.5 \text{ V}$		170	380	μΑ
Shut down supply current *1	I <sub>CCSD</sub>	$V_{I} = 0.5 \text{ V},$ $V_{IO} \ge V_{SD} \ge V_{IO} - 0.3 \text{ (SD = High)}$		10	200	nA
Maximum reception distance *4	L <sub>max</sub>	$V_{SD} \le 0.5 \text{ V}$ , External components	23	40		cm
RC maximum reception distance	L <sub>maxR</sub>	$RC S = 0.05 \mu W/cm^2$	5			m
Data Rates			9.6		115.2	kbps
SD high level input voltage	V <sub>IHSD</sub>		V <sub>IO</sub> - 0.5		V <sub>IO</sub>	V
SD low level input voltage	V <sub>ILSD</sub>		0		0.5	V

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### $\blacksquare \ \, \text{Electrical-Optical Characteristics (Continued)} \ \, V_{CC} = 3.2 \ V, \, V_{IO} = 1.8 \ V, \, T_a = 25^{\circ} \text{C} \pm 3^{\circ} \text{C}$

Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Transmitter						!	
Peak emission wavelength *1		$\lambda_{\mathrm{P}}$	$V_{SD} \le 0.5 \text{ V, Duty } 3/16 \text{ (IrDA mode)}$	878	883	888	nm
			$V_{SD} \le 0.5 \text{ V}$ , Duty 25% (RC mode)	878	894	910	nm
Pulse forward current *1		$I_{\mathrm{FP}}$	$V_{SD} \le 0.5 \text{ V},$ I-TXD Duty 3/16, R-TXD $\le 0.5 \text{ V},$ (IrDA mode)	40	60	90	mA
			$V_{CC} = 4.2 \text{ V, } V_{SD} \le 0.5 \text{ V,}$ R-TXD Duty 25%, I-TXD $\le 0.5 \text{ V,}$ (RC mode)	240	270	300	mA
			$\begin{aligned} &V_{CC} = 3.2 \text{ V, } V_{SD} \leq 0.5 \text{ V,} \\ &R\text{-TXD Duty 25\%, I-TXD} \leq 0.5 \text{ V,} \\ &(\text{RC mode}) \end{aligned}$	190	220	250	mA
Center radiant intensity *1, 2, 9	$\theta_{\mathrm{T}} = 0$	Ie	$V_{CC} = 3.2 \text{ V}, V_{SD} \le 0.5 \text{ V},$ I-TXD Duty 3/16, R-TXD $\le$ 0.5 V, (IrDA mode)	9	20		mW/sr
			$\begin{split} &V_{CC} = 4.2 \text{ V, } V_{SD} \leq 0.5 \text{ V,} \\ &R\text{-TXD Duty 25\%, I-TXD} \leq 0.5 \text{ V,} \\ &(\text{RC mode}) \end{split}$	40	73	110	mW/sr
			$V_{CC} = 3.2 \text{ V, } V_{SD} \le 0.5 \text{ V,}$ R-TXD Duty 25%, I-TXD $\le 0.5 \text{ V,}$ (RC mode)	36	68	102	mW/sr
	$\theta_{\rm T} = \pm 15$	I <sub>e15</sub>	$V_{CC} = 3.2 \text{ V}, V_{SD} \le 0.5 \text{ V},$ I-TXD Duty 3/16, R-TXD $\le 0.5 \text{ V},$ (IrDA mode)	6	10		mW/sr
			$V_{CC} = 4.2 \text{ V}, V_{SD} \le 0.5 \text{ V},$ R-TXD Duty 25%, I-TXD $\le 0.5 \text{ V},$ (RC mode)	28	40	63	mW/sr
			$V_{CC} = 3.2 \text{ V}, V_{SD} \le 0.5 \text{ V},$ R-TXD Duty 25%, I-TXD $\le 0.5 \text{ V},$ (RC mode)	28	38	60	mW/sr
High level input voltage *1		N/	I-TXD	$V_{IO}-0.5$		V <sub>IO</sub>	V
riign ievei input voitage		V <sub>IH</sub>	R-TXD	V <sub>IO</sub> -0.5		V <sub>IO</sub>	V
Low level input voltage *1		$V_{\rm IL}$		0		0.5	V
TX half-angle		$\theta_{\mathrm{T}}$		±15			0
Rise time *1,3		t <sub>r</sub>	$t_{\rm w} = 1.6 \ \mu \rm s, \ R_{\rm L} = 50 \ \Omega$		0.3	0.6	μs
Fall time *1,3		$t_{\mathrm{f}}$	$t_{\rm w} = 1.6 \ \mu \rm s, \ R_{\rm L} = 50 \ \Omega$		0.3	0.6	μs
TX wake up time *7		$t_{Twu}$			0.3	1	μs
Intensity delay time *1,3		$I_{DT}$				400	ns
Maximum pulse width		T <sub>wLEDmax</sub>	I-TXD, R-TXD = Low $\rightarrow$ High	20	50	100	μs
Overshoot		$O_S$				25	%
Edge jitter		$E_{J}$		-40		40	ns

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### $\blacksquare \ \, \text{Electrical-Optical Characteristics (Continued)} \ \, V_{CC} = 3.2 \ V, \, V_{IO} = 1.8 \ V, \, T_a = 25 ^{\circ} C \pm 3 ^{\circ} C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Receiver						
Minimum input irradiance	E <sub>I min</sub>	$V_{SD} \le 0.5 \text{ V}$		2.2	6.8	μW/cm <sup>2</sup>
Maximum input irradiance	E <sub>I max</sub>	$V_{SD} \le 0.5 \text{ V}$	500			mW/cm <sup>2</sup>
High level output voltage *5	V <sub>OH</sub>	Non signal condition $I_{OH} = -200~\mu\text{A},  V_{SD} \leq 0.5~\text{V}$	V <sub>IO</sub> -0.3		V <sub>IO</sub>	V
Low level output voltage *6	V <sub>OL</sub>	$I_{OL} = 200 \mu A, V_{SD} \le 0.5 \text{ V}$			0.3	V
RX half angle	$\theta_{R}$		±15			0
RXD output pulse width	$T_{WR}$	$C_L = 15 \text{ pF}, 9.6 \text{ kbps to } 115.2 \text{ kbps}$	1.3	2.3	4.2	μs
RX wake up time *8	t <sub>Rwu</sub>	$E_I = 8.1 \ \mu W/cm^2$		250	400	μs
Rise time	t <sub>r</sub>	$C_L = 15 \text{ pF}$		100	300	ns
Fall time	$t_{\mathrm{f}}$	$C_L = 15 \text{ pF}$		100	300	ns

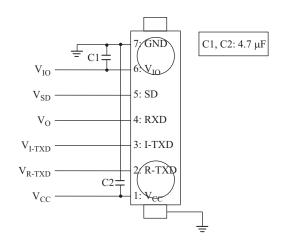
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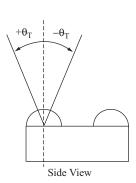
### ■ Electrical-Optical Characteristics (Continued)

Note) Measuring circuit

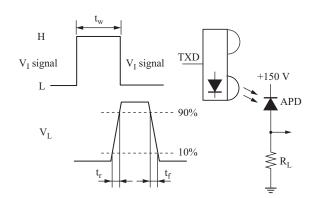
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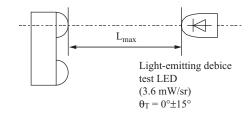
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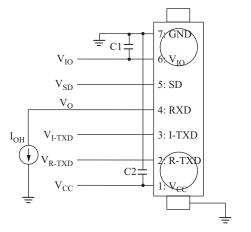
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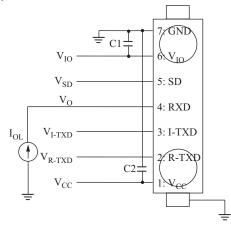
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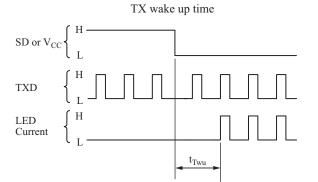
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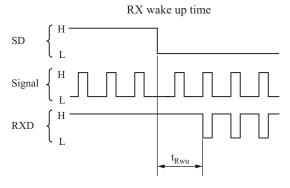
\*6:



\*7:



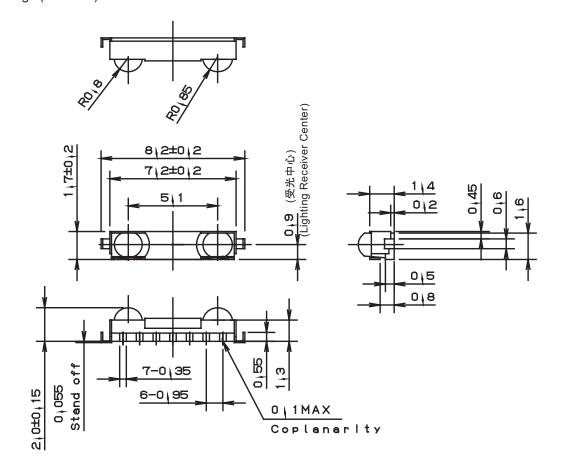
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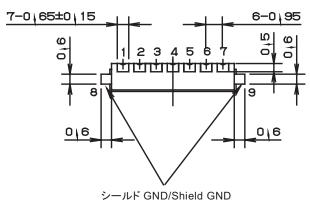


\*9: Eye-Safety IEC60825-1 Class1 Eye safe

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### ■ Package (Unit: mm)





#### • Pin name

 $1.\ V_{CC} \qquad \qquad 6.\ V_{IO}$ 

2. R-TXD 7. GND

3. I-TXD 8. Shield GND

4. RXD 9. Shield GND

5. SD

# 



### ■ This product contains Gallium Arsenide (GaAs).

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